

Data Sheet	January 2002	

30A, 200V Ultrafast Dual Diode

The RURG3020CC is an ultrafast dual diode with soft recovery characteristics (t_{rr} < 45ns). It has low forward voltage drop and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristics minimizes ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

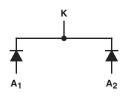
Formerly developmental type TA09645.

Ordering Information

PART NUMBER	PACKAGE	BRAND	
RURG3020CC	TO-247	RURG3020C	

NOTE: When ordering, use the entire part number.

Symbol



Features

•	Ultrafast with Soft Recovery	<45ns
•	Operating Temperature	175 ⁰ C
•	Reverse Voltage	.200V

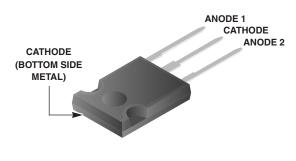
- Avalanche Energy Rated
- Planar Construction

Applications

- · Switching Power Supplies
- · Power Switching Circuits
- General Purpose

Packaging

JEDEC STYLE TO-247



Absolute Maximum Ratings (Per Leg) T_C = 25°C RURG3020CC **UNITS** 200 200 200 30 $(T_C = 145^{\circ}C)$ 70 Α (Square Wave, 20kHz) Nonrepetitive Peak Surge Current IFSM 325 (Halfwave, 1 Phase, 60Hz) 125 W 20 mJ -65 to 175 οС

RURG3020CC

Electrical Specifications (Per Leg) $T_C = 25^{\circ}C$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V _F	I _F = 30A	-	-	1.0	V
	I _F = 30A, T _C = 150°C	-	-	0.85	V
I _R	V _R = 200V	-	-	250	μΑ
	V _R = 200V, T _C = 150 ^o C	-	-	1	mA
t _{rr}	$I_F = 1A$, $dI_F/dt = 100A/\mu s$	-	-	45	ns
	$I_F = 30A$, $dI_F/dt = 100A/\mu s$	-	-	50	ns
t _a	$I_F = 30A$, $dI_F/dt = 100A/\mu s$	-	20	-	ns
t _b	$I_F = 30A$, $dI_F/dt = 100A/\mu s$	-	15	-	ns
$R_{ heta JC}$		-	-	1.2	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

I_R = Instantaneous reverse current.

 t_{rr} = Reverse recovery time (See Figure 6), summation of $t_a + t_b$.

 t_a = Time to reach peak reverse current (See Figure 6).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

Typical Performance Curves

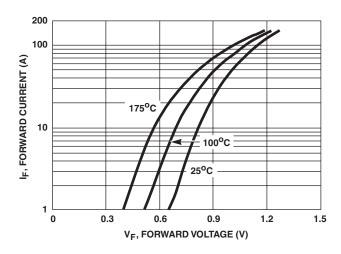


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

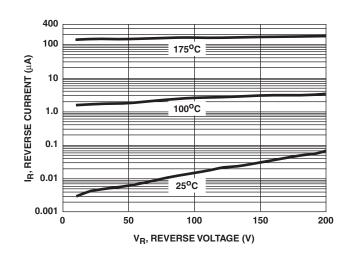


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

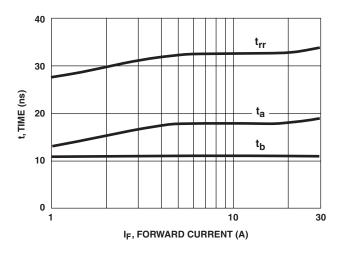


FIGURE 3. t_{rp}, t_a AND t_b CURVES vs FORWARD CURRENT

(V) 40 DC DC SQ. WAVE 10 130 140 150 160 170 180 T_C, CASE TEMPERATURE (°C)

FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

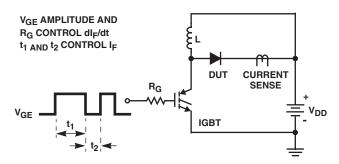


FIGURE 5. t_{rr} TEST CIRCUIT

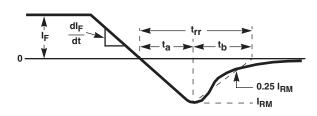


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

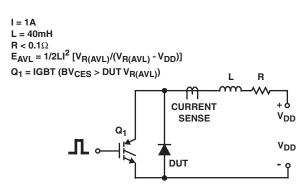


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

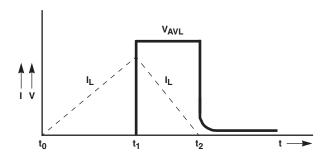


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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